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To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572
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Subject: | Serial No. 09/579,542 05/26/00 |

Cheng Chung Lin, Lain-Jong Li

METHOD TO IMPROVE STABILITY AND
RELIABILITY OF CVD LOW K DIELECTRIC

Grp. Art Unit:

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

The Applied Materials website for 3/4/00 gives reference
to "Black Diamond".

U.S. Patent 5,593,741 to Ikeda, "Method and Apparatus for
Forming Silicon Oxide Film by Chemical Vapor Deposition",
discloses a low K CVD process that varies the RF power during
deposition and flows oxygen gas.

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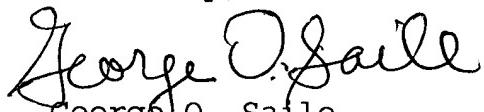
U.S. Patent 5,514,624 to Morozumi, "Method of Manufacturing a Microelectronic Interlayer Dielectric Structure", discloses a low k oxide layer using an organosilicate reactant and an oxygen flow.

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U.S. Patent 5,432,129 to Hodges, "Method of Forming Low Resistance Contacts at the Junction Between Regions Having Different Conductivity Types", discloses an oxygen densification step for an oxide.

U.S. Patent 4,992,306 to Hochberg et al., "Deposition of Silicon Dioxide and Silicon Oxynitride Films Using Azidosilane Sources", discloses a PECVD SiO₂ process.

Sincerely,


George O. Saile,
Reg. No. 19572